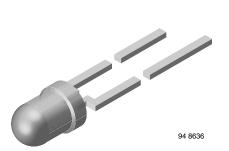


Vishay Semiconductors

High Speed Infrared Emitting Diode, RoHS Compliant, 890 nm, GaAlAs Double Hetero



DESCRIPTION

TSHF4410 is an infrared, 890 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

Package type: leadedPackage form: T-1

Dimensions (in mm): Ø 3
Peak wavelength: λ_D = 890 nm

· High reliability

· High radiant power

· High radiant intensity

• Angle of half intensity: $\phi = \pm 22^{\circ}$

· Low forward voltage

• Suitable for high pulse current operation

• High modulation bandwidth: f_c = 12 MHz

· Good spectral matching with Si photodetectors

 Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC



- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK coded, 450 kHz or 1.3 MHz)
- · Smoke-automatic fire detectors

PRODUCT SUMMARY					
COMPONENT	I _e (mW/sr)	φ (deg)	λ _P (nm)	t _r (ns)	
TSHF4410	40	± 22	890	30	

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
TSHF4410	Bulk	MOQ: 5000 pcs, 5000 pcs/bulk	T-1		

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	5	V	
Forward current		I _F	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \ \mu s$	I _{FM}	200	mA	
Surge forward current	t _p = 100 μs	I _{FSM}	1.5	Α	
Power dissipation		P _V	180	mW	
Junction temperature		Tj	100	°C	





ROHS COMPLIAN

Vishay Semiconductors High Speed Infrared Emitting Diode, RoHS Compliant, 890 nm, GaAlAs Double Hetero



ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Operating temperature range		T _{amb}	- 40 to + 85	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	$t \le 5 \text{ s}, 2 \text{ mm from case}$	T _{sd}	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R _{thJA}	300	K/W	

Note

T_{amb} = 25 °C, unless otherwise specified

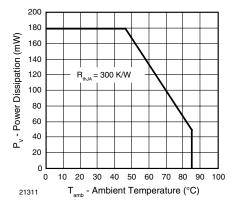


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

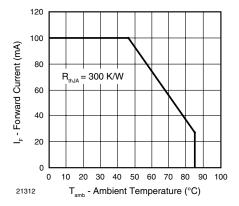


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Farmers well-see	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V _F		1.5	1.8	V
Forward voltage	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	V _F		2.4	1.5 1.8	V
Temperature coefficient of V _F	I _F = 1 mA	TK _{VF}		- 1.8		mV/K
Reverse current	V _R = 5 V	I _R			10	μΑ
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	Cj		125		pF
Padiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l _e		40		mW/sr
Radiant intensity	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	l _e		400		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фе		40		mW
Temperature coefficient of ϕ_e	I _F = 100 mA	TKφe		- 0.35		%/K
Angle of half intensity		φ		± 22		deg
Peak wavelength	I _F = 100 mA	λρ		890		nm
Spectral bandwidth	I _F = 100 mA	Δλ		44		nm
Temperature coefficient of λ_p	I _F = 100 mA	TKλ _p		0.25		nm/K
Rise time	I _F = 100 mA	t _r		30		ns
Fall time	I _F = 100 mA	t _f		30		ns
Cut-off frequency	$I_{DC} = 70 \text{ mA}, I_{AC} = 30 \text{ mA pp}$	f _c		12		MHz
Virtual source diameter	Method: 63 % encircled energy	d		1.9		mm

Note

 T_{amb} = 25 °C, unless otherwise specified



High Speed Infrared Emitting Diode, RoHS Vishay Semiconductors Compliant, 890 nm, GaAlAs Double Hetero

BASIC CHARACTERISTICS

T_{amb} = 25 °C, unless otherwise specified

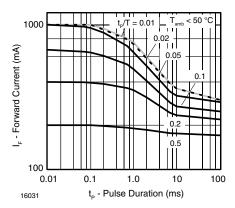


Fig. 3 - Pulse Forward Current vs. Pulse Duration

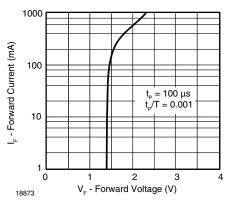


Fig. 4 - Forward Current vs. Forward Voltage

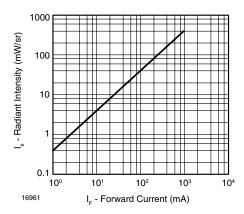


Fig. 5 - Radiant Intensity vs. Forward Current

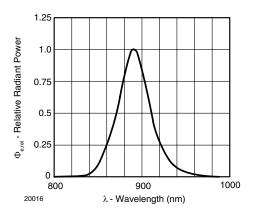


Fig. 6 - Relative Radiant Power vs. Wavelength

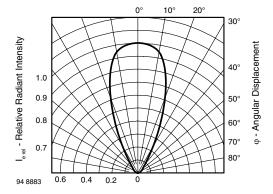
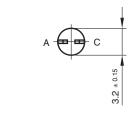


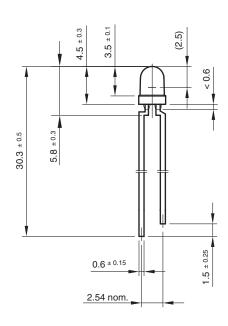
Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

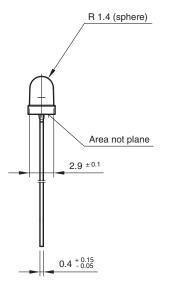
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PACKAGE DIMENSIONS in millimeters









technical drawings according to DIN specifications

Drawing-No.: 6.544-5255.01-4

Issue: 6; 24.07.08

95 10913





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